



Vanadium Dioxide Design Solution for Ultrafast Switches

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WARF: P170254US01

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The Wisconsin Alumni Research Foundation (WARF) is seeking commercial partners interested in developing vanadium dioxide-based switches characterized by isostructural metal-insulator transition near room temperature.

This technology overcomes a longstanding challenge and potentially enables devices with unprecedented speed and endurance.

Overview

The unique properties of vanadium dioxide (VO_2) mean it could one day outperform silicon and enable next-generation, ultralow-power devices. A key advantage of this material is that above 341 kelvin – near room temperature – bulk VO_2 is a metal. But as soon as the material is cooled below 341 k, VO_2 turns into an insulator. The superfast change in resistance means that VO_2 could be very powerful in a variety of applications involving high speed optoelectronic switches.

However, the metal-insulator transition is accompanied by an undesirable change in crystal structure from rutile to monoclinic, which to date has limited the material's practical applications.

The Invention

UW-Madison researchers have designed VO_2 heterostructures capable of metal-insulator transition near room temperature in practical thin films. The heterostructures are made of multiple bilayers of VO_2 engineered to have different rutile-to-monoclinic structural transition temperatures.

The bilayers can be incorporated into a variety of electrical switches including capacitors, planar switches and field effect switches, in integrated circuits for memory devices (e.g., CMOS chips) and communication devices. In each of these devices the conversion of the bilayer from its electrically insulating to conducting metallic state (and vice versa) changes the resistance/conductance of the bilayer, thereby modulating current flow or capacitance.

Applications

- Optoelectronic switches, Mott transistors, femtosecond switches and more

Key Benefits

- Maximizes the potential of VO_2 as a next-generation material

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WARF believes that these technologies are especially attractive opportunities for licensing.

Additional Information

For More Information About the Inventors

- [Chang-Beom Eom](#)

Related Technologies

- [Find more thin-film innovations developed by Prof. Chang-Beom Eom](#)

Publications

- [Lee D. et al. 2018. Isostructural Metal-Insulator Transition in VO₂. Science 6418, 1037-1040.](#)
- [Read a news story about this technology.](#)

Tech Fields

- [Semiconductors & Integrated Circuits : Components & materials](#)
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For current licensing status, please contact Michael Carey at mcarey@warf.org or 608-960-9867

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